

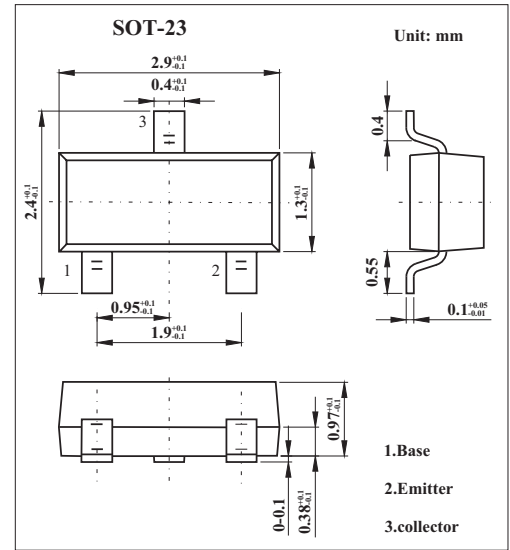
SOT-23 Plastic-Encapsulate Transistors

Features

- High Voltage Transistors
- NPN Silicon

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V_{CE0}	200	V
Collector-base voltage	V_{CB0}	200	V
Emitter-base voltage	V_{EB0}	6	V
Collector current-continuous	I_C	500	mA
Total device dissipation FR-5 board *1			
@TA = 25°C	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	556	°C/W
Total device dissipation alumina substrate *2			
@TA = 25°C	P_D	300	mW
derate above 25°C		2.4	mW/°C
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	417	°C/W
Junction and storage temperature	T_J, T_{stg}	-55 to +150	°C

PACKAGE INFORMATION

Device	Package	Shipping
MBTA43	SOT-23	3000/Tape&Reel

* 1. FR-5 = 1.0 X 0.75 X 0.062 in.

* 2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage *	$V_{(BR)CE0}$	$I_C = 1.0 \text{ mA}, I_E = 0$	200			V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu\text{A}, I_E = 0$	200			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	6			V
Collector cutoff current	I_{CBO}	$V_{CB} = 160 \text{ V}, I_E = 0$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 4.0 \text{ V}, I_C = 0$			0.1	μA
DC current gain *	h_{FE}	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$	25			
		$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	40			
		$I_C = 30 \text{ mA}, V_{CE} = 10 \text{ V}$	40			
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 20 \text{ mA}, I_B = 2.0 \text{ mA}$			0.5	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = 20 \text{ mA}, I_B = 2.0 \text{ mA}$			0.9	V
Current-gain - bandwidth product	f_T	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V}, f = 100 \text{ MHz}$	50			MHz
Collector-base capacitance	C_{cb}	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$			4	pF

* Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Marking

Marking	M1E